

FIG. 1

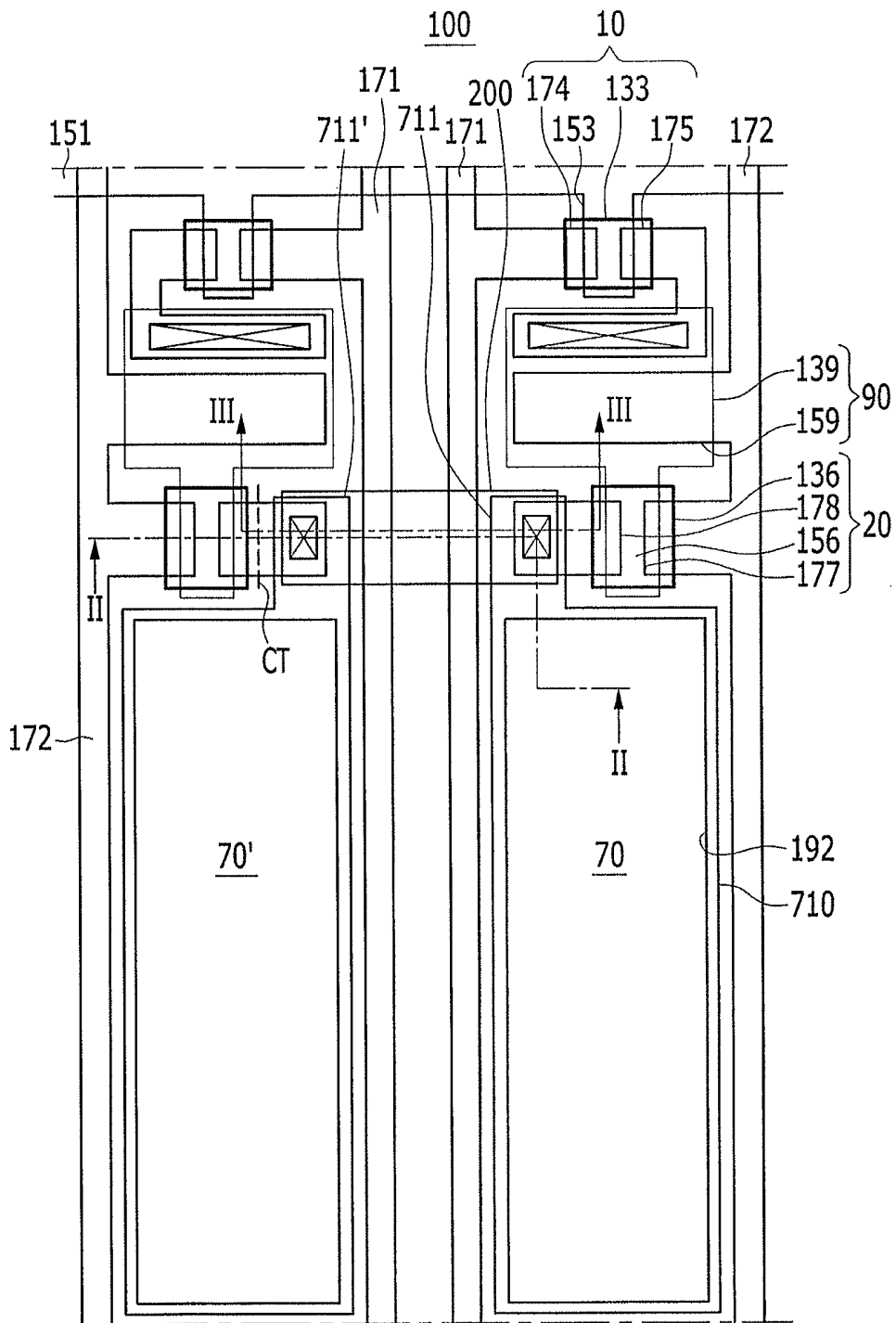


FIG. 2

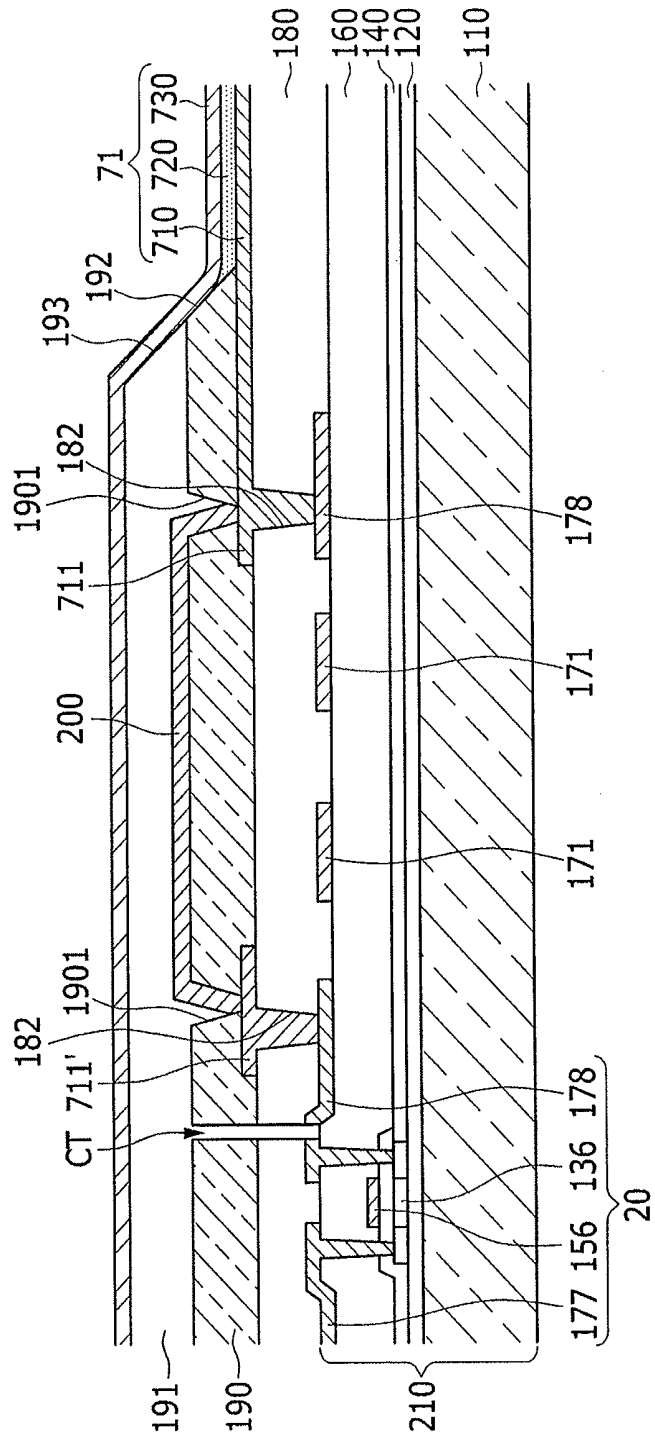


FIG. 3A

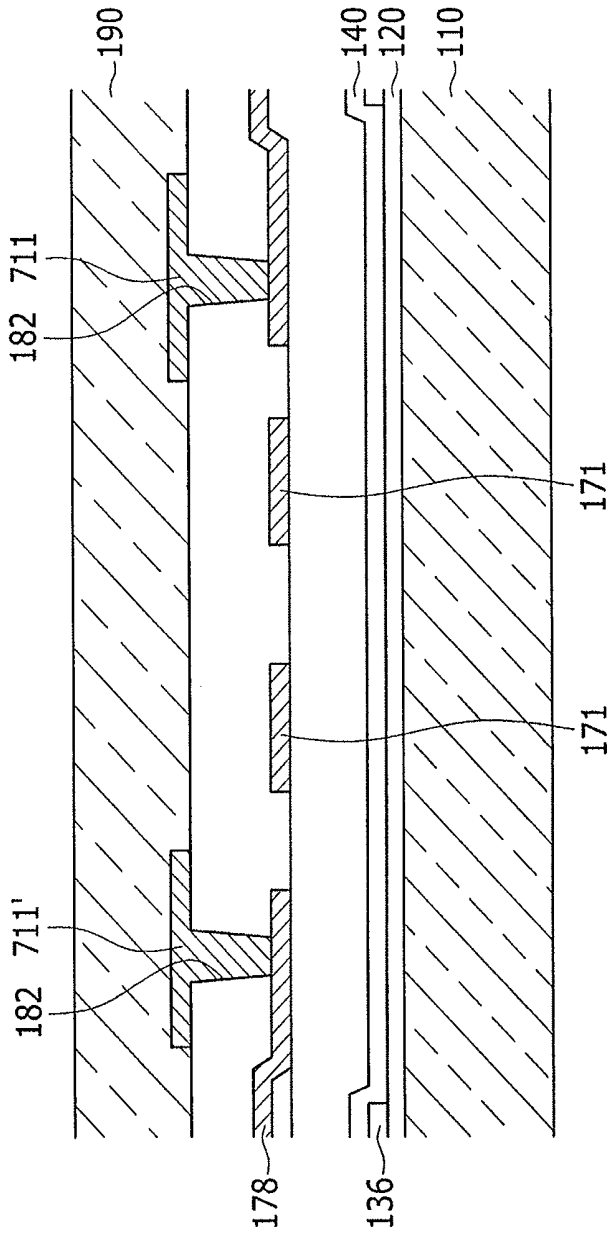


FIG. 3B

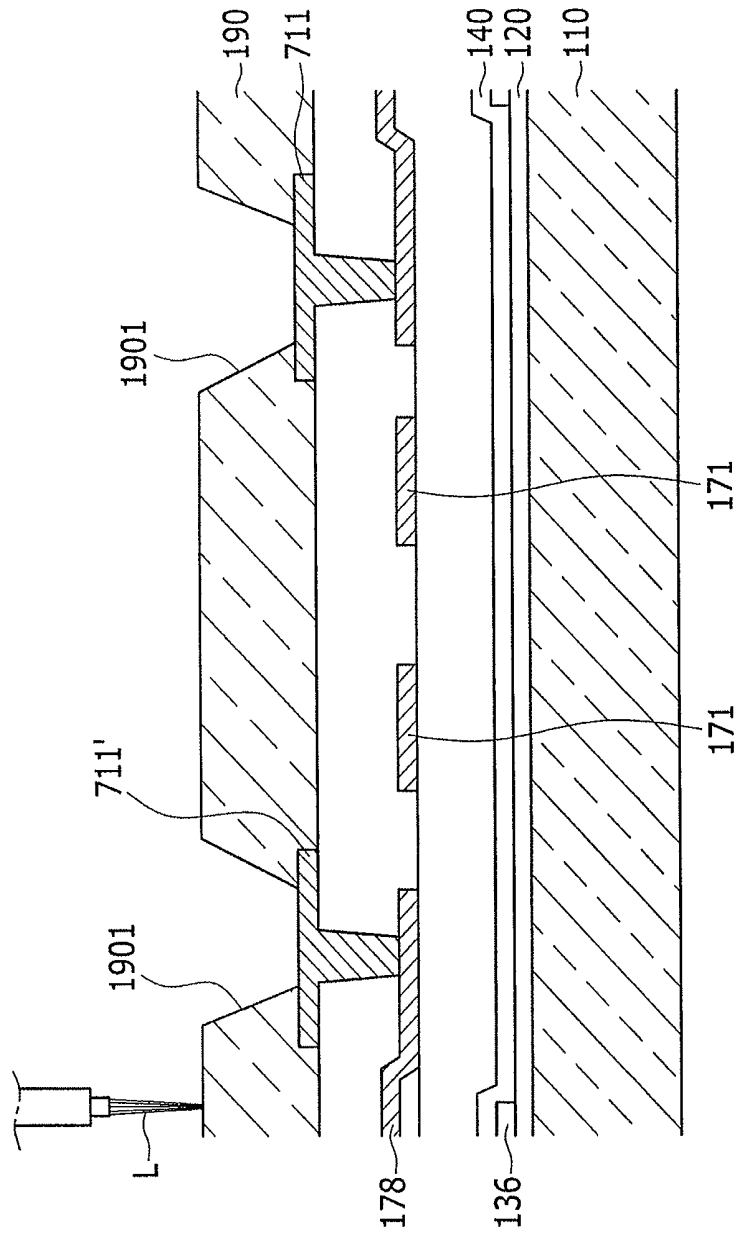


FIG. 3C

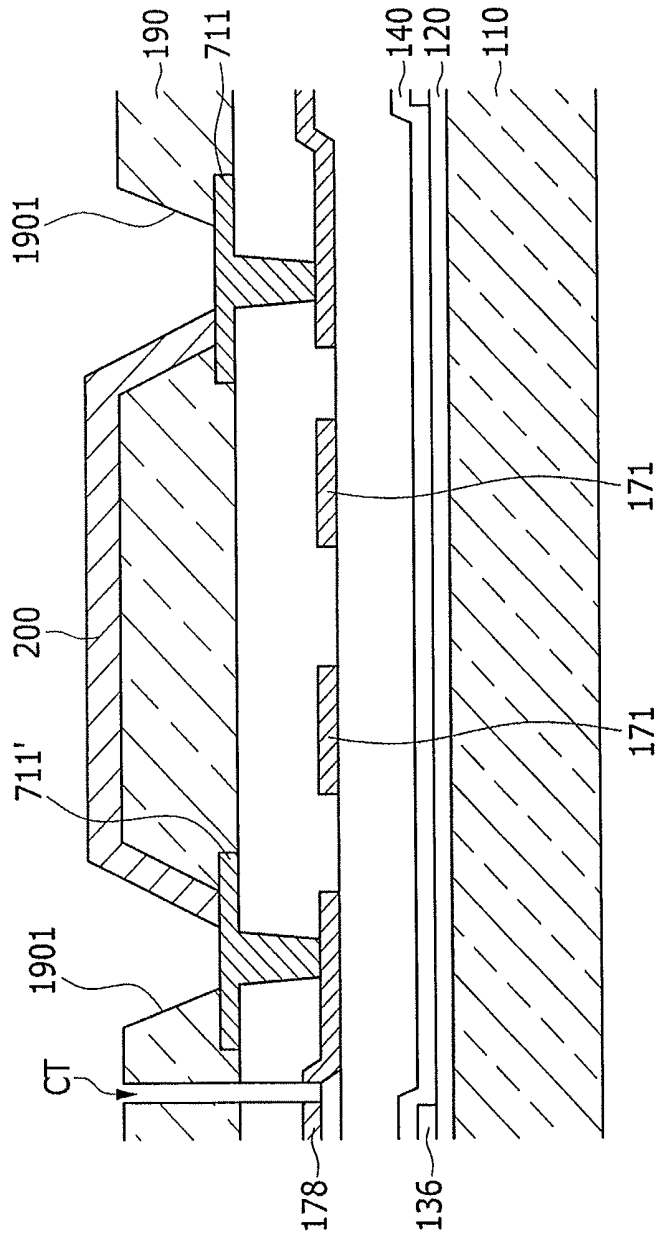
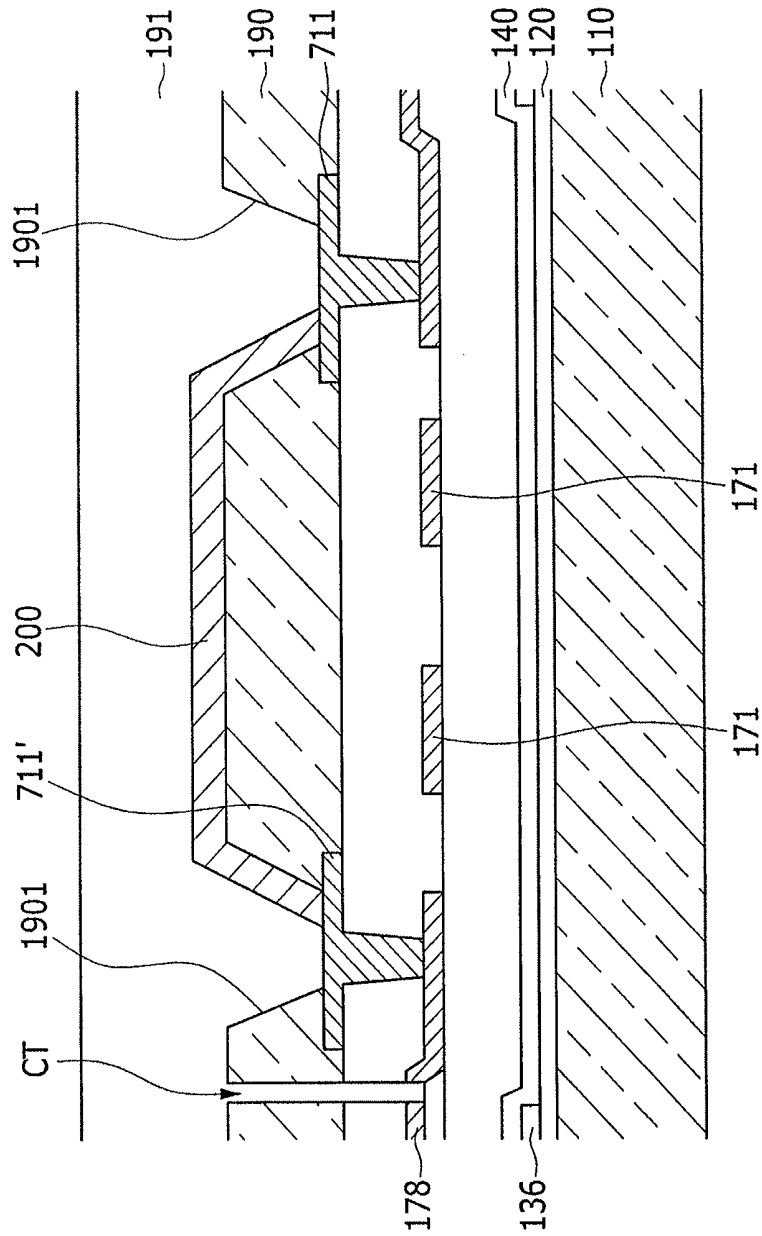


FIG. 3D



METHOD FOR MANUFACTURING ORGANIC LIGHT EMITTING DISPLAY DEVICE

CROSS-REFERENCE TO RELATED APPLICATION

This is a divisional application based on pending application Ser. No. 13/602,410, filed Sep. 4, 2012, the entire contents of which is hereby incorporated by reference.

This application claims priority to and the benefit of Korean Patent Application No. 10-2012-0027319 filed in the Korean Intellectual Property Office on Mar. 16, 2012, the entire contents of which are incorporated herein by reference.

BACKGROUND

The described technology relates generally to an organic light emitting diode (OLED) display and a manufacturing method thereof.

SUMMARY

Embodiments are directed to an organic light emitting diode (OLED) display, including a substrate having a plurality of pixels, a first pixel defining layer on the substrate, the first pixel defining layer dividing the plurality of pixels, a connection wire on the first pixel defining layer, the connection wire electrically connecting two adjacent pixels, and a second pixel defining layer on the first pixel defining layer, the second pixel defining layer covering the connection wire.

Each of the plurality of pixels may include a pixel electrode and a pixel terminal extending from the pixel electrode. The first pixel defining layer may include one or more connection holes exposing respective pixel terminals of the two adjacent pixels.

The connection wire may electrically connect the two adjacent pixels through the connection holes.

One of the two adjacent pixels may be a defective pixel and the another one of the two adjacent pixels may be a normal pixel. The defective pixel may be driven by a signal applied to the normal pixel.

A plurality of thin film transistors may be provided between the substrate and each pixel terminal to supply a signal for driving each pixel. The normal pixel of the two adjacent pixels may be electrically connected with a respective one of the thin film transistors corresponding to the normal pixel. The defective pixel of the two adjacent pixels may be electrically disconnected from a respective one of the thin film transistors corresponding to the defective pixel.

The connection wire may include at least one of tungsten, chromium, molybdenum, aluminum, titanium, and tantalum, or an alloy thereof.

The first pixel defining layer may include a plurality of first openings to expose each the pixel electrode. The second pixel defining layer may include a plurality of second openings to expose each pixel electrode.

The second pixel defining layer may be disposed to fill the connection holes.

The second pixel defining layer may be disposed between pixel terminals of the two adjacent pixels.

Pixel terminals of the two adjacent pixels may be exposed through a single connection hole. The first pixel defining layer may include a first portion formed in a connection hole and a second portion relatively thicker than the first portion.

The second pixel defining layer may cover the first portion. An upper side of the second pixel defining layer and an upper side of the second portion of the first pixel defining layer may correspond to each other.

Embodiments are also directed to a manufacturing method of an organic light emitting diode (OLED) display, the manufacturing method including forming a plurality of pixels and a plurality of thin film transistors electrically connected to the plurality of pixels, respectively, on a substrate, forming a first pixel defining layer dividing the plurality of pixels, detecting a defective pixel by testing the plurality of pixels, disconnecting an electrical connection between the defective pixel and a respective one of the thin film transistors, forming a connection wire for electrical connection between the defective pixel and a pixel adjacent to the defective pixel, and forming a second pixel defining layer on the first pixel defining layer to cover the connection wire.

The pixels may respectively include pixel electrodes and pixel terminals extended from the pixel electrodes. The thin film transistors may be electrically connected with the pixel terminals.

The forming of the connection wire may include forming a connection hole by removing a portion of the first pixel defining layer to expose the defective pixel and the pixel terminal of the pixel that is adjacent to the defective pixel.

The forming of the connection wire may include connecting the pixel terminal of the defective pixel and the pixel terminal of the pixel that is adjacent to the defective pixel with the connection wire through the connection hole.

The forming of the connection wire may include depositing at least one of tungsten, chromium, molybdenum, aluminum, titanium, and tantalum, or an alloy thereof using a chemical vapor deposition method.

The disconnecting the electrical connection between the defective pixel and the respective one of the thin film transistors may include cutting the electrical connection using a laser.

Each thin film transistor may include a semiconductor layer, a source electrode, and a drain electrode, the source electrode and the drain electrodes contacting the semiconductor layer. The disconnecting of the electrical connection between the defective pixel and the respective one of the thin film transistors includes cutting the source electrode or the drain electrode.

BRIEF DESCRIPTION OF THE DRAWINGS

Features will become apparent to those of skill in the art by describing in detail exemplary embodiments with reference to the attached drawings in which:

FIG. 1 illustrates a layout view of a pixel structure of an organic light emitting diode display according to an exemplary embodiment.

FIG. 2 illustrates a cross-sectional view of FIG. 1, taken along the line II-II.

FIG. 3A to FIG. 3D illustrate cross-sectional views of FIG. 1, taken along the line and illustrate a process for restoring a failure in a manufacturing process of the OLED display according to the exemplary embodiment.

FIG. 4 illustrates a cross-sectional view of a part of an OLED display according to another exemplary embodiment.

DETAILED DESCRIPTION

Example embodiments will now be described more fully hereinafter with reference to the accompanying drawings; however, they may be embodied in different forms and should not be construed as limited to the embodiments set forth herein. Rather, these embodiments are provided so that this disclosure will be thorough and complete, and will fully convey the scope thereof to those skilled in the art.

Throughout the specification, like reference numerals designate like elements throughout the specification.

It shall be noted that the drawings are schematic and do not depict exact dimensions. The relative proportions and ratios of elements in the drawings may be exaggerated or diminished in size for the sake of clarity and convenience in the drawings, and such arbitrary proportions are only illustrative and not limiting in any way. Like reference numerals are used for like structures, elements, or parts shown in two or more drawings to show similar characteristics. When one part is said to be "over" or "on" another part, the one part may be directly over the other part or may be accompanied by another part interposed therebetween.

Exemplary embodiments specifically show preferred exemplary embodiments. As a result, various modifications of the drawings are anticipated. Accordingly, exemplary embodiments are not limited to certain forms of the regions illustrated, but may include forms that are modified through manufacturing, for example.

Hereinafter, an organic light emitting diode display according to an exemplary embodiment will be described with reference to FIG. 1 and FIG. 2.

FIG. 1 is a layout view of a pixel structure of an organic light emitting diode (OLED) display according to an exemplary embodiment.

As shown in FIG. 1, an OLED display 100 according to the exemplary embodiment includes a plurality of pixel areas. Each pixel may have a 2 Tr-1 Cap structure with an organic light emitting diode 71, two thin film transistors 10 and 20, and a capacitor 90. Here, the term "pixel area" may refer to a unit area where a pixel, which is a minimum unit for displaying an image, is formed. However, in other configurations, the pixel may be variously modified.

For example, each pixel area of the OLED display 100 may have a structure in which three or more thin film transistors and two or more capacitors are provided. In addition, the OLED display 100 may include additional connecting lines, such that the OLED display 100 may have various structures. At least one of additionally formed thin film transistors and capacitors may constitute a compensation circuit. The compensation circuit may improve the uniformity of the OLED 71 formed in the pixel areas PE so as to suppress image quality deviation. The compensation circuit may include two to eight thin film transistors.

In further detail, in the exemplary embodiment, the OLED display 100 may include a first thin film transistor 10 and a second thin film transistor 20 formed in each pixel area. The first thin film transistor 10 and the second thin film transistor 20 may respectively include gate electrodes 153 and 156, active layers 133 and 136, source electrodes 174 and 177, and drain electrodes 175 and 178.

A gate line 151, a data line 171, and a common power line 172 may be formed on a substrate 110. Each pixel area may be defined by the gate line 151, the data line 171, and the common power line 172. However, in other implementations, the pixel area may be variously modified. In addition, although it is not illustrated, a capacitor line may be additionally formed on the substrate 110.

A source electrode 174 of the first thin film transistor 10 may be connected to the data line 171, and a gate electrode 153 of the first thin film transistor 10 may be connected to the gate line 151. A node may be formed between a drain electrode 175 of the first thin film transistor 10 and a capacitor 90 such that the drain electrode 175 of the first thin film transistor 10 is connected with a first capacitor electrode 139 of the capacitor 90. A second capacitor electrode 159 may be connected with the common power line 172. The drain electrode

175 of the first thin film transistor 10 may be connected with the gate electrode 156 of the second thin film transistor 20. The common power line 172 may be connected to a source electrode 177 of the second thin film transistor 20, and an anode of the organic light emitting element 70 may be connected to the drain electrode 178.

The organic light emitting element 70 may include the anode, which may be a hole injection electrode, a cathode, which may be an electron injection electrode, and an organic emission layer 720 provided between the anode and the cathode. Meanwhile, according to a driving method, locations of the anode and the cathode of the organic light emitting element may be switched. Hereinafter, in the exemplary embodiment, the anode is a pixel electrode 710 and the cathode is a common electrode 730.

The first thin film transistor 10 may be used as a switch for selecting a pixel area for light emission. When the first thin film transistor 10 is instantly turned on, the capacitor 90 is charged, and the amount of the charge charged at this time is proportional to the potential of the voltage applied from the data line 171. In addition, a gate potential of the second thin film transistor 20 is increased according to a potential charged in the capacitor 90 while the first thin film transistor 10 is in the turned-off state. The second thin film transistor 20 is turned on when the gate potential exceeds a threshold voltage. Then, a voltage applied to the common power line 172 is applied to the organic light emitting element 71 through the second thin film transistor 20 such that the organic light emitting element 71 emits light.

The structure of the pixel PE may be variously modified.

The structure of the OLED display according to the exemplary embodiment will be described in further detail with reference to FIG. 1 and FIG. 2.

FIG. 2 is a cross-sectional view of FIG. 1, taken along the line II-II.

As shown in FIG. 2, a buffer layer 120 may be formed on the substrate 110. The buffer layer 120 may be formed through chemical vapor deposition or physical vapor deposition and may have a single-layered structure or a multi-layered structure including various insulating layers, such as a silicon oxide film, silicon nitride film, and the like. The buffer layer 120 may serve to prevent moisture or impurities generated from the substrate 110 from spreading or infiltrating beyond the substrate 110. The buffer layer 120 may also smooth the surface of the substrate 110, and regulate a heat transfer speed during a crystallization process performed for forming the active layers to thus accomplish desirable crystallization. The buffer layer 120 may be omitted according to the type and process condition of the substrate 110.

The active layers 133 and 136 and the first capacitor electrode 139 may be formed on the buffer layer 120. An amorphous silicon layer may be formed on the buffer layer 120, crystallized, and then patterned such that the active layers 133 and 136 and the first capacitor electrode 139 are formed. However, in other implementations, the first capacitor electrode 139 and the active layer 139 may be formed of different materials, as desired.

A gate insulating layer 140 may be formed on the active layers 133 and 136 and the first capacitor electrode 139. In further detail, the gate insulating layer 140 may be formed to cover the active layers 133 and 136 and the first capacitor electrode 139 on the buffer layer 120. The gate insulating layer 140 may be formed including at least one of various suitable insulation materials, such as tetra ethyl ortho silicate (TEOS), silicon nitride (SiN_x), and silicon oxide (SiO_2).

The gate line 151 including gate electrodes 153 and 156 and a second capacitor electrode 159 may be formed on the

gate insulating layer **140**. The gate electrode **153** and **156** may at least partially overlap the active layers **133** and **136**.

An interlayer insulating layer **160** may be formed on the gate insulating layer **140** to cover the gate electrodes **153** and **156**, the second capacitor electrode **159**, and gate line **151**. The gate insulating layer **140** and the interlayer insulating layer **160** may have through-holes to partially expose the active layers **133** and **136**. The interlayer insulating layer **160** and the gate insulating layer **140** may be formed of the same material.

The data line **171**, which may include source electrodes **174** and **177** and drain electrodes **175** and **178** and the common power line **172**, may be formed on the interlayer insulating layer **160**. The source electrodes **174** and **177** and the drain electrodes **175** and **178** may be connected with the active layers **133** and **136** through the through-holes formed in the interlayer insulating layer **160** and the gate insulating layer **140**.

As described, the first and second thin film transistors **10** and **20** including the active layers **133** and **136**, the gate electrodes **153** and **156**, the source electrodes **174** and **177**, and the drain electrodes **175** and **178** and the wire portions **210** including the gate line **151**, the data line **171**, the common power line **172**, and the capacitor **90** may be formed. The configuration of the wire portion **210** may be variously modified.

A protection insulating layer **180** may be formed on the interlayer insulating layer **160** to cover the source electrodes **174** and **177**, the drain electrodes **175** and **178**, and the data line **171**. The protection insulating layer **180** may be formed of various suitable materials. The protection insulating layer **180** may have a contact hole **182** that partially exposes the drain electrode **178** of the second thin film transistor **20**. The configuration of the protection insulating layer **180** may be varied. In other implementations, one of the protection insulating layer **180** and the interlayer insulating layer **160** may be omitted or the protection insulating layer **180** may be partially cover the wire portion **210**.

A pixel electrode **710** of the organic light emitting element **71** and a pixel terminal **711** extended from the pixel electrode **710** may be formed on the protection insulating layer **180**. That is, the OLED display **100** may include a plurality of pixel electrodes **710** disposed at a distance from each other in each of the plurality of pixel areas. The pixel terminal **711** may be connected with the drain electrode **178** through the contact hole **182** of the protection insulating layer **180**. The configurations of the pixel electrode **710** and the pixel terminal **711** may be varied. For example, the pixel electrode **710** and the pixel terminal **711** may be formed on the interlayer insulating layer **160** or on the gate insulating layer **140**, and the pixel terminal **711** may have a single-layered or multi-layered structure.

In addition, a first pixel defining layer having a plurality of first openings **192** that expose the pixel electrode **710** of each pixel area may be formed on the protection insulating layer **180**. The first pixel defining layer **190** may be formed of various suitable organic or inorganic materials. For example, the first pixel defining layer **190** may be formed by patterning a photosensitive organic layer and thermally or optically baking the patterned photosensitive organic layer.

The organic emission layer **720** may be formed on the pixel electrode **710** on the first opening **192** of the first pixel defining layer **190**.

The first pixel defining layer **190** may have a connection hole **1901** that exposes the pixel terminal **711**. A connection wire **200** and a second pixel defining layer **191** may be formed on the first pixel defining layer **190**. The connection hole

1901, the connection wire **200**, and the second pixel defining layer **191** will be described in detail below.

A common electrode **730** may be formed on the organic emission layer **720** and the first and second pixel defining layers **190** and **191**. Thereby, the organic light emitting element **71** including the pixel electrode **710**, the organic emission layer **720**, and the common electrode **730** may be formed. The organic emission layer **720** may be formed of a low molecular organic material or a high molecular organic material, and may be formed as a plurality of organic layers including an emission layer. The pixel electrode **710** and the common electrode **730** may be respectively formed of a transparent conductive material or may be formed of a semitransparent or reflective conductive material. The OLED display **100** may be a top emission type, a bottom emission type, or a double-sided emission type according to the kind of the materials that form the first electrode **710** and the second electrode **730**. Such a configuration of the organic light emitting element **70** may be variously modified.

At least one of the plurality of pixel areas of the OLED display **100** may include the connection wire **200** electrically connected with a neighboring pixel area. That is, a defective pixel having an emission problem in a pixel area may be produced during a manufacturing process of the OLED display **100**. The defective pixel may be noticeable as a dark spot in the completed OLED display **100** if the defective pixel is not repaired during the manufacturing process. Herein, the term "defective pixel" may refer to a pixel that functions to emit light when provided with a driving signal, but for various reasons, such as a defect in a corresponding transistor or signal line, does not receive the normal driving signal. Thus, the defective pixel may be driven to emit light by electrically connecting the pixel with a normal pixel adjacent thereto, thereby repairing the defective pixel for normal operation according to a signal transmitted to the normally operating pixel.

In FIG. 1 and FIG. 2, the pixel area having the defect is indicated by reference numeral **70'** (hereinafter, referred to as a "defective pixel") and a normal pixel area adjacent to the defective pixel is indicated by reference numeral **70** (hereinafter, referred to as a "normal pixel"). In addition, a pixel terminal of the defective pixel is indicated by reference numeral **711'**, and a pixel terminal of the adjacent normal pixel is indicated by reference numeral **711**.

As shown in FIG. 2, the first pixel defining layer **190** may include connection holes **1901** that expose the pixel terminal **711'** of the defective pixel **70'** and the pixel terminal **711** of the normal pixel **70**. The connection wire **200** that connects the pixel terminal **711'** of the defective pixel **70'** and the pixel terminal **711** of the normal pixel **70** through the connection holes **1901** may be formed on the first pixel defining layer **190**. The connection wire **200** may include at least one material selected from tungsten (W), chromium (Cr), molybdenum (Mo), aluminum (Al), titanium (Ti), and tantalum (Ta), or may include an alloy thereof.

In the defective pixel **70'**, the pixel terminal **711'** and the thin film transistor **20** are disconnected. In further detail, the pixel terminal **711'** of the defective pixel **70'** is manufactured to include an electric connection with the drain electrode **178** of the second thin film transistor **20** through the contact hole **182** of the protection insulating layer **180**. Accordingly, in order to block the application of a defective signal to an organic light emitting element of the defective pixel **70a**, a cutting portion CT may be formed in the drain electrode **177** between the pixel terminal **711'** and the second thin film transistor **20'**. The cutting portion CT in the present exemplary embodiment may be formed at a portion where the drain

electrode **178** is connected with the pixel terminal **711'** and at a portion where the drain electrode **178** is not connected with the pixel terminal **711'**. In further detail, the cutting portion CT may be formed as a hole that separates the drain electrode **178**, as described above, while penetrating to the drain electrode **178** from the first pixel defining layer **190**. The configuration of the cutting portion CT can be modified in various suitable configurations to block a signal applied to the defective pixel **70'** from the second thin film transistor **20**.

The second pixel defining layer **191** may be formed on the first pixel defining layer **190** to cover the connection wire **200**. Like the first pixel defining layer **190**, the second pixel defining layer **191** may include a second opening **193** that exposes the pixel electrode **710**. In addition, the second pixel defining layer **191** may be formed to thoroughly fill the connection hole **1901** and the cutting portion CT formed in the first pixel defining layer **190**.

Like the first pixel defining layer **190**, the second pixel defining layer **191** may be formed of various organic or inorganic materials, and, for example, may be formed by patterning a photosensitive organic layer and thermally or optically baking the patterned photosensitive organic layer.

With such a configuration, the defective pixel **70'** may operate by the same signal as the normal signal applied to the normal pixel **70**. In the OLED display **100**, although the defective pixel **70'** is generated due to a failure in a thin film transistor in one pixel area, the defective pixel **70'** may emit light together with the adjacent normal pixel **70** by a normal signal applied through the normal pixel **70**.

Accordingly, in the OLED display **100** according to the present exemplary embodiment, the defective pixel generated during the manufacturing process may not appear as a dark spot.

Hereinafter, a method for recovering a defective pixel in a manufacturing process of the OLED display according to the exemplary embodiment will be described with reference to FIG. 3A to FIG. 3D.

FIG. 3A to FIG. 3D are cross-sectional views of a process for recovering the failure in the manufacturing process of the OLED display according to the exemplary embodiment, taken along the line III-III of FIG. 1.

As shown in FIG. 3A, the wire portion **210** (refer to FIG. 2) may be formed on the substrate **110**. The pixel electrode **710** (refer to FIG. 2) and the pixel terminals **711** and **711'** extended from the pixel electrode **710** and contacting the drain electrode **178** may be formed on the wire portion **210**. The pixel defining layer **190** covering the pixel terminals **711** and **711'** and having the plurality of first openings **192** (refer to FIG. 2) that expose the pixel electrode **710** may be formed.

After the first pixel defining layer **190** is formed, the plurality of pixel areas are tested to detect a defective pixel **70'**. In order to detect the defective pixel **70'**, various testing methods, such as, for example, an auto optical inspection, an array test, and the like, may be performed.

Subsequently, as shown in FIG. 3B, the connection hole **1901** may be formed to expose the pixel terminal **711'** of the defective pixel **70'** and the pixel terminal **711** of the normal pixel **70** that is adjacent to the pixel terminal **711'**. The connection hole **1901** may be formed by patterning a photosensitive organic layer. The connection hole **1901** may have any size that can establish electrical contact between the pixel terminals **711** and **711'**.

In addition, in order to block a signal applied to the pixel terminal **711'**, the cutting portion CT (refer to FIG. 3c) may be formed using a laser L to separate the drain electrode **177** of the defective pixel **70'**.

Subsequently, as shown in FIG. 3C, the connection wire **200** electrically connecting the pixel terminals **711** and **711'** may be formed. The connection wire **200** may be formed to directly contact the pixel terminals **711** and **711'** through the connection hole **1901** on the first pixel defining layer **190**. The connection wire **200** may be formed through deposition of at least one selected from tungsten (W), chromium (Cr), molybdenum (Mo), aluminum (Al), titanium (Ti), and tantalum (Ta) or an alloy thereof using a chemical vapor deposition (CVD) method. For example, a CVD wiring method using tungsten (W) may be used. The forming of the connection wire **200** may be variously modified in various suitable configurations.

Subsequently, as shown in FIG. 3D, the second pixel defining layer **191** may be formed on the first pixel defining layer **190** to cover the connection wire **200**. Like the first pixel defining layer **190**, the second pixel defining layer **191** may be formed throughout the pixel area excluding an area of the second opening **193** (refer to FIG. 2) that exposes the pixel electrode **710** (refer to FIG. 2). However, the second pixel defining layer **191** may be formed in any area as long as the second pixel defining layer **191** covers the connection wire **200**.

According to the manufacturing method of the OLED display including the failure recovering method, a failure occurring during the manufacturing process of the OLED display may be easily recovered. Therefore, the number of dark spots in the OLED display may be reduced, and a product yield of the OLED display may be improved.

Hereinafter, an OLED display **100'** according to a second exemplary embodiment will be described with reference to FIG. 4.

FIG. 4 is a cross-sectional view of a part of the OLED display according to this exemplary embodiment, corresponding to the cross-section of FIG. 1, taken along the like II-II.

As shown in FIG. 4, in the OLED display **100'** according to this exemplary embodiment, a second pixel defining layer **191'** may be formed only between a pixel terminal **711'** of a defective pixel **70'** and a pixel terminal **711** of a normal pixel **70**. That is, in this exemplary embodiment, a first pixel defining layer **190'** has a first portion **1902** formed in a connection hole **1901'** and a second portion **1903** that is different from the first portion **1902** and has a step. Here, the first portion **1902** and the second portion **1903** are separated from each other, and the second pixel defining layer **191'** has a first portion **1902** that is relatively thinner than the second portion **1902**.

Here, the second pixel defining layer **191'** fills the connection hole **1901'** over the connection wire **200** such that an upper side of the second pixel defining layer **191'** substantially corresponds to an upper side of the first pixel defining layer **190'**.

Meanwhile, the OLED display **100'** according to this exemplary embodiment is substantially equivalent to the OLED display **100** according to the exemplary embodiment, excluding that the second pixel defining layer **191'** may be formed only between the pixel terminal **711'** of the defective pixel **70'** and the pixel terminal **711** of the normal pixel **70**.

By way of summation and review, an OLED display may incur a defect during a stage of a manufacturing process, such that a dark spot may be present at a pixel. Typically, a pixel having the defect cannot be easily repaired during the manufacturing process.

Thus, when a display device having a defect in a pixel is provided to a user, the defective pixel is recognized as a dark spot by a user such that user satisfaction may be degraded. Although a pixel having a defect may be detected during the manufacturing process, it may not be possible to repair the

pixel, and thus, the OLED display including the pixel may be discarded, causing economical and environmental problems.

The described embodiments may provide an organic light emitting diode (OLED) display that may reduce the number of dark spots by enabling the repair of a defect occurring during a manufacturing process. Further, the described embodiments may provide a method for manufacturing an OLED display that may improve a product yield by simply recovering a failure that may occur during a manufacturing process. Accordingly, user satisfaction may be improved. In addition, according to the exemplary embodiments, the product yield of the OLED display may be improved, and thus, productivity may be improved. OLED displays having defective pixels may not need to be discarded, and accordingly, an environment problem may be prevented.

Example embodiments have been disclosed herein, and although specific terms are employed, they are used and are to be interpreted in a generic and descriptive sense only and not for purpose of limitation. In some instances, as would be apparent to one of ordinary skill in the art as of the filing of the present application, features, characteristics, and/or elements described in connection with a particular embodiment may be used singly or in combination with features, characteristics, and/or elements described in connection with other embodiments unless otherwise specifically indicated. Accordingly, it will be understood by those of skill in the art that various changes in form and details may be made without departing from the spirit and scope of the present invention as set forth in the following claims.

What is claimed is:

1. A manufacturing method of an organic light emitting diode (OLED) display, the manufacturing method comprising:
 forming a plurality of pixels and a plurality of thin film transistors electrically connected to the plurality of pixels, respectively, on a substrate;
 forming a first pixel defining layer dividing the plurality of pixels;
 detecting a defective pixel by testing the plurality of pixels;
 disconnecting an electrical connection between the defective pixel and a respective one of the thin film transistors;

forming a connection wire for electrical connection between the defective pixel and a pixel adjacent to the defective pixel; and

forming a second pixel defining layer on the first pixel defining layer to cover the connection wire, wherein: the pixels respectively include pixel electrodes and pixel terminals extended from the pixel electrodes, the thin film transistors are electrically connected with the pixel terminals, and

forming the connection wire includes forming a connection hole by removing a portion of the first pixel defining layer to expose the defective pixel and the pixel terminal of the pixel that is adjacent to the defective pixel.

2. The manufacturing method of the OLED display of claim 1, wherein the forming of the connection wire includes connecting the pixel terminal of the defective pixel and the pixel terminal of the pixel that is adjacent to the defective pixel with the connection wire through the connection hole.

3. The manufacturing method of the OLED display of claim 1, wherein the forming of the connection wire includes depositing at least one of tungsten, chromium, molybdenum, aluminum, titanium, and tantalum, or an alloy thereof using a chemical vapor deposition method.

4. The manufacturing method of the OLED display of claim 1, wherein the disconnecting the electrical connection between the defective pixel and the respective one of the thin film transistors includes cutting the electrical connection using a laser.

5. The manufacturing method of the OLED display of claim 1, wherein:

each thin film transistor includes a semiconductor layer, a source electrode, and a drain electrode, the source electrode and the drain electrodes contacting the semiconductor layer, and

the disconnecting of the electrical connection between the defective pixel and the respective one of the thin film transistors includes cutting the source electrode or the drain electrode.

* * * * *

专利名称(译)	制造有机发光显示装置的方法		
公开(公告)号	US9356086	公开(公告)日	2016-05-31
申请号	US14/550596	申请日	2014-11-21
[标]申请(专利权)人(译)	三星显示有限公司		
申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
当前申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
[标]发明人	JIN GUANG HAI CHOI JAE BEOM JUNG KWAN WOOK LEE JUNE WOO KIM MOO JIN KIM GA YOUNG		
发明人	JIN, GUANG HAI CHOI, JAE-BEOM JUNG, KWAN-WOOK LEE, JUNE-WOO KIM, MOO-JIN KIM, GA-YOUNG		
IPC分类号	H01L27/00 H01L51/00 H01L27/32		
CPC分类号	H01L27/3276 H01L27/3246 H01L51/0031 H01L2227/323		
优先权	1020120027319 2012-03-16 KR		
其他公开文献	US20150079703A1		
外部链接	Espacenet USPTO		

摘要(译)

有机发光二极管(OLED)显示器包括其中形成多个像素的基板,基板上的第一像素限定层,划分多个像素的第一像素限定层,第一像素限定层上的连接线,连接电线连接两个相邻像素,第二像素限定层位于第一像素限定层上,第二像素限定层覆盖连接线。

